

The documentation and process conversion measures necessary to comply with this revision shall be completed by 12 December 1997.

INCH POUND

MIL-PRF-19500/503B
12 September 1997
SUPERSEDING
MIL-S-19500/503A
12 April 1993

PERFORMANCE SPECIFICATION SHEET

SEMICONDUCTOR DEVICE, DIODE, SILICON, POWER RECTIFIER,
ULTRA FAST RECOVERY, TYPES 1N6073 THROUGH 1N6081,
JAN, JANTX, JANTXV, AND JANHC

This specification is approved for use by all Departments and Agencies of the Department of Defense.

1. SCOPE

1.1 Scope. This specification covers the performance requirements for three separate series of silicon, ultra fast recovery semiconductor diodes for use as power rectifiers. Three levels of product assurance are provided for each device as specified in MIL-PRF-19500. One level of product assurance is provided for die.

1.2 Physical dimensions. See figures 1 (similar to D0-35) and 2 (die) herein.

1.3 Maximum ratings.

Types	V_R	V_{RWM}	I_{O1} $T_A = +55^\circ\text{C}$ 3/ 4/ 5/	I_O $T_L = +70^\circ\text{C}$ 1/ 2/ 3/	t_{rr} $I_F = 0.5\text{ A}$ $I_R = -1.0\text{ A}$ $I_{RR} = -0.25\text{ A}$	T_{STG} and T_J	$R_{\theta JL}$ 1/	I_{FSM} $t_p = 8.3\text{ ms}$
	<u>V dc</u>	<u>V (pk)</u>	<u>A dc</u>	<u>A dc</u>	<u>ns</u>	<u>°C</u>	<u>°C/W</u>	<u>A (pk)</u>
1N6073	50	50	0.85	3.0	30	-65 to +155	13.0	35
1N6074	100	100	0.85	3.0	30	-65 to +155	13.0	35
1N6075	150	150	0.85	3.0	30	-65 to +155	13.0	35
1N6076	50	50	1.3	6.0	30	-65 to +155	8.5	75
1N6077	100	100	1.3	6.0	30	-65 to +155	8.5	75
1N6078	150	150	1.3	6.0	30	-65 to +155	8.5	75
1N6079	50	50	2.0	12.0	30	-65 to +155	5.0	175
1N6080	100	100	2.0	12.0	30	-65 to +155	5.0	175
1N6081	150	150	2.0	12.0	30	-65 to +155	5.0	175

1/ I_O and $R_{\theta JL}$ rating at $L = 0$ and without forced air across the device body and/or leads.

2/ Derate I_O rating to zero current linearly, from $T_L = 70^\circ\text{C}$, to $+150^\circ\text{C}$.

3/ Higher I_O rating is allowable provided that T_L and/or T_A is maintained such that $T_J \leq 155^\circ\text{C}$.

4/ I_O rating without heat sinking, special mounting or forced air across the device body and/or leads.

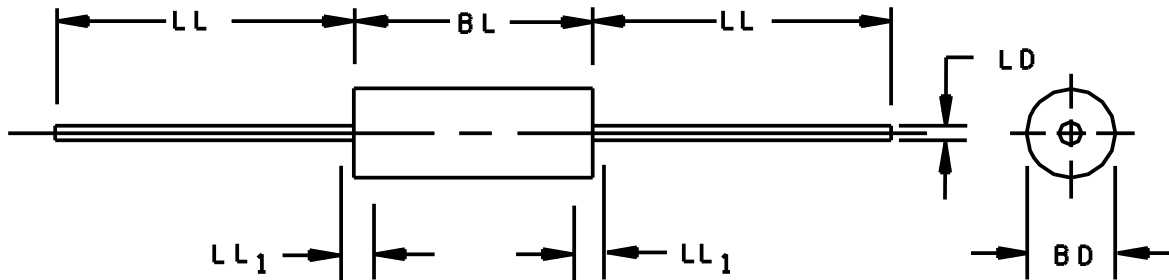
5/ Derate I_O rating to zero current linearly, from $T_A = +55^\circ\text{C}$, to $+155^\circ\text{C}$.

Beneficial comments (recommendations, additions, deletions) and any pertinent data which may be of use in improving this document should be addressed to: Commander, Defense Supply Center Columbus, ATTN: DSCC-VAT, 3990 East Broad St., Columbus, OH 43216-5000, by using the addressed Standardization Document Improvement Proposal (DD Form 1426) appearing at the end of this document or by letter.

AMSC N/A

DISTRIBUTION STATEMENT A. Approved for public release; distribution is unlimited.

FSC 5961

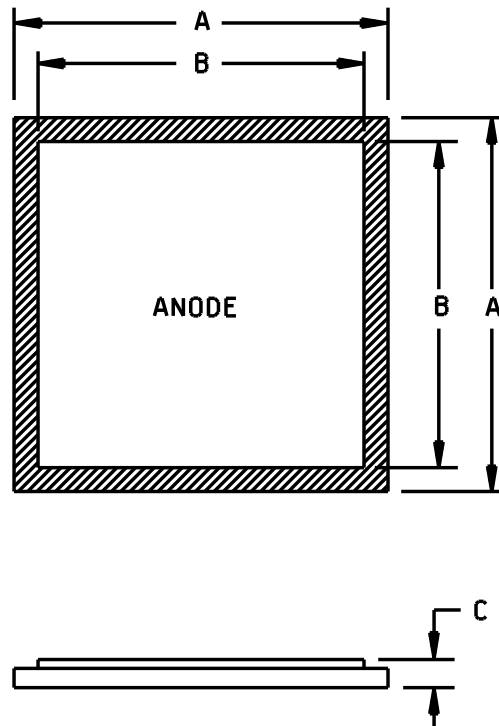


Symbol	Dimensions												Notes
	1N6073 THROUGH 1N6075				1N6076 through 1N6078				1N6079 through 1N6081				
	Inches		Millimeters		Inches		Millimeters		Inches		Millimeters		
	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
BD	0.055	0.083	1.40	2.16	0.065	0.140	1.65	3.56	0.135	0.190	3.43	4.83	3
LD	0.026	0.033	0.66	0.84	0.036	0.042	0.91	1.07	0.036	0.042	0.91	1.07	
BL	0.140	0.225	3.56	5.72	0.140	0.225	3.56	5.72	0.140	0.225	3.56	5.72	
LL	1.00	1.30	25.40	33.02	0.90	1.30	22.90	33.02	0.090	1.30	22.90	33.02	
M		0.03		0.76		0.03		0.76		0.03		0.76	4

NOTES:

1. Dimensions are in inches.
2. Metric equivalents are given for general information only.
3. Dimension BD shall be measured at the largest diameter.
4. The LL1 dimension shall include all uncontrolled areas of the device.

FIGURE 1. Physical dimensions.



Symbol	Dimensions											
	1N6073 THROUGH 1N6075 (see note 3)				1N6076 through 1N6078 (see note 4)				1N6079 through 1N6081 (see note 4)			
	Inches		Millimeters		Inches		Millimeters		Inches		Millimeters	
	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max
A	0.039	0.043	0.99	1.09	0.066	0.070	1.68	1.78	0.128	0.132	3.25	3.35
B	0.031	0.035	0.79	0.89	0.057	0.061	1.45	1.55	0.119	0.123	3.02	3.12
C	0.008	0.012	0.20	0.30	0.008	0.012	0.20	0.30	0.008	0.012	0.20	0.30

NOTES:

1. Dimensions are in inches.
2. Metric equivalents are given for general information only.
3. Anode thickness: AL - 45,000 Å minimum; cathode thickness: AU - 2500 Å minimum.
4. Anode thickness: AL - 60,000 Å minimum; cathode thickness: AU - 2500 Å minimum.

FIGURE 2. Physical dimensions, JANHC (A - version).

2. APPLICABLE DOCUMENTS

2.1 General. The documents listed in this section are specified in sections 3 and 4 of this specification. This section does not include documents cited in other sections of this specification or recommended for additional information or as examples. While every effort has been made to ensure the completeness of this list, document users are cautioned that they must meet all specified requirements documents cited in sections 3 and 4 of this specification, whether or not they are listed.

2.2 Specifications, standards, and handbooks. The following specifications, standards, and handbooks form a part of this document to the extent specified herein. Unless otherwise specified, the issues of these documents are those listed in the issue of the Department of Defense Index of Specifications and Standards (DODISS) and supplement thereto, cited in the solicitation (see 6.2).

SPECIFICATION

DEPARTMENT OF DEFENSE

MIL-PRF-19500 - Semiconductor Devices, General Specification for.

STANDARD

MILITARY

MIL-STD-750 - Test Methods for Semiconductor Devices.

MIL-STD-1276 - Leads for Electronic Component Parts.

(Unless otherwise indicated, copies of the above specifications, standards, and handbooks are available from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.3 Order of precedence. In the event of a conflict between the text of this document and the references cited herein (except for related associated specifications or specification sheets), the text of this document takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

3.1 Associated specification. The individual item requirements shall be in accordance with MIL-PRF-19500, and as specified herein.

3.2 Abbreviations, symbols, and definitions. Abbreviations, symbols, and definitions shall be as specified in MIL-PRF-19500.

3.3 Interface requirements and physical dimensions. The Interface requirements and physical dimensions shall be as specified in MIL-PRF-19500, and figures 1 (similar to D0-35) and 2 (die) herein.

3.3.1 Diode construction. The diode shall be metallurgically bonded, non-cavity, double plug construction.

3.3.2 Lead finish. Lead finish shall be solderable as defined in MIL-PRF-19500, MIL-STD-750, and as specified herein. Where a choice of lead finish is desired, it shall be specified in the acquisition document (see 6.2).

3.4 Marking. Marking shall be in accordance with MIL-PRF-19500. At the option of the manufacturer, the following marking may be omitted from the body of the diode, but shall be retained on the initial container.

a. "1N" of the type designation.

3.5 Polarity. The polarity of all types shall be indicated with a contrasting color band to denote the cathode end.

3.6 Electrical performance characteristics. Unless otherwise specified herein, the electrical performance characteristics are as specified in paragraph 1.3, 1.4, and table I.

3.7 Electrical test requirements. The electrical test requirements shall be the subgroups specified in paragraphs 4.4.2 and 4.4.3.

MIL-PRF-19500/503B

3.8 Qualification. Devices furnished under this specification shall be products that are authorized by the qualifying activity for listing on the applicable qualified products list before contract award (see 4.2 and 6.2).

4. VERIFICATION

4.1 Classification of Inspections. The inspection requirements specified herein are classified as follows:

- a. Qualification inspection (see 4.2).
- b. Screening (see 4.3).
- c. Conformance inspection (see 4.3).

4.2 Qualification inspection. Qualification inspection shall be in accordance with MIL-PRF-19500.

4.2.1 JANHC devices. Qualification for JANHC devices shall be in accordance with MIL-PRF-19500.

4.3 Screening (JANTX and JANTXV levels). Screening shall be in accordance with table IV of MIL-PRF-19500, and as specified herein. The following measurements shall be made in accordance with table I herein. Devices that exceed the limits of table I herein shall not be acceptable.

Screen (see table IV of MIL-PRF-19500)	Measurement
	JANTX and JANTXV levels
9	Not applicable
10	$T_A = 125^\circ \text{C}$
11	V_F and I_{R1}
12	See 4.3.1
13	Subgroup 2 of table I herein; $\Delta V_{F1} = \pm 0.1 \text{ V dc}$; $\Delta I_{R1} = 1/$ or 100 percent of the initial value, whichever is greater. Scope display evaluation (see 4.5.3).

1/ ΔI_{R1} is as follows:

- for 1N6073 through 1N6075 = +0.250 $\mu\text{A dc}$.
- for 1N6076 through 1N6078 = +1.0 $\mu\text{A dc}$.
- for 1N6079 through 1N6081 = +5.0 $\mu\text{A dc}$.

4.3.1 Power burn-in conditions. Power burn-in conditions are as follows: MIL-STD-750, method 1038, $T_A = +25^\circ \text{C}$ (minimum); $V_{RWM} = \text{rated } V_{RWM}$ (see 1.3); $I_O = \text{rated } I_{O1}$ (see 1.3); $f \geq 60 \text{ Hz}$.

4.3.2 Screening (JANHC). Screening of JANHC die shall be in accordance with MIL-PRF-19500.

4.4 Conformance inspection. Conformance inspection shall be in accordance with MIL-PRF-19500.

4.4.1 Group A inspection. Group A inspection shall be conducted in accordance with MIL-PRF-19500 and table I herein.

MIL-PRF-19500/503B

4.4.2 Group B inspection. Group B inspection shall be conducted in accordance with the conditions specified for subgroup testing in table VIb (JAN, JANTX, and JANTXV) of MIL-PRF-19500 and as follows. Electrical measurements (end-points) and delta requirements shall be in accordance with the applicable steps of table II herein.

4.4.2.1 Group B inspection, table VIb of MIL-PRF-19500.

Subgroup	Method	Condition
2	4066	I_{FSM} = rated I_{FSM} (see 1.3); 10 surges of 8.3 ms each at 1 minute intervals, superimposed on I_{O1} (see 1.3); V_{RWM} = rated V_{RWM} (see 1.3).
3	1026	(see 4.5.5); T_A = +55° C minimum, I_{O1} = rated I_{O1} (see 1.3); f = 60 Hz; V_{RWM} = rated V_{RWM} (see 1.3), mounting conditions (see 4.5.5.1 and 4.5.5.2).
5	4081	+25° C $\leq T_R \leq$ 35° C; R_{OJL} at L = 0 inches, (see 1.3).

4.4.3 Group C inspection. Group C inspection shall be conducted in accordance with the conditions specified for subgroup testing in table VII of MIL-PRF-19500 and as follows. Electrical measurements (end-points) and delta requirements shall be in accordance with the applicable steps of table II herein.

Subgroup	Method	Condition
2	2036	(tension) test condition A, t = 15s, for 1N6073 through 1N6075 weight = 10 lbs, for 1N6076 through 1N6081, weight = 20 lbs.
6	1026	(see 4.5.5); T_A = +55° C minimum, I_{O1} = rated I_{O1} (see 1.3); f = 60 Hz; V_{RWM} = rated V_{RWM} (see 1.3), mounting conditions (see 4.5.5.1 and 4.5.5.2).

4.5 Methods of inspection. Methods of inspection shall be specified in the appropriate tables and as follows.

4.5.1 Pulse measurements. Conditions for pulse measurement shall be as specified in section 4 of MIL-STD-750.

4.5.2 Inspection conditions. Unless otherwise specified, all inspections shall be conducted at an ambient temperature T_A of +25° C \pm 3° C.

4.5.3 Scope display evaluation. The reverse breakdown characteristics shall be viewed on an oscilloscope with display calibration factors of 20 μ A/division and 10 to 50 V/division. Reverse current over the knee shall be at least 100 μ A. Each device may exhibit a sharp knee characteristic and any discontinuity or dynamic instability of the trace shall be cause for rejection.

4.5.4 Reverse-recovery time. The reverse recovery time shall be measured in the circuit of figure 3 or an equivalent circuit. The recovery conditions shall be 0.5 A forward current to 1.0 A reverse current. The reverse recovery time is defined as the time the rectifier begins to conduct in the reverse direction (crosses I = zero) until the reverse current decays to - 0.25 A. The point of contact on the leads shall be no less than .375 inch (9.52 mm) from the diode body.

4.5.5 Steady-state operation life. This test shall be conducted with a half-sine waveform of the specified peak voltage impressed across the diode in the reverse direction, followed by a half-sine waveform of the specified average rectified current. The forward conduction angle of the rectified current shall be no greater than 180 degrees nor less than 150 degrees.

4.5.5.1 Mounting conditions. The diodes shall be suspended by the leads with at least 6 inches of No. 22 gauge wire between each lead and the power source. The connecting wires may be soldered to the end of the diode leads or MS27491 removable contacts may be used. Other contacts may be used provided they have equal or less mass than the MS27491 contacts. Ambient temperature shall be maintained at the specified temperature. No forced air shall be permitted, and the diodes shall be shielded from drafts.

4.5.5.2 Alternate mounting conditions. At the option of the manufacturer, other clip or heatsink mounting configurations may be used provided the I_O is adjusted such that each device junction temperature +125° C $\leq T_J \leq$ +155° C at an ambient temperature +25° C $\leq T_A \leq$ +55° C.

MIL-PRF-19500/503B

TABLE I. Group A inspection.

	MIL-STD-750			Limits		
Inspection	Method	Conditions	Symbol	Min	Max	Unit
<u>Subgroup 1</u>						
Visual and mechanical inspection	2071					
<u>Subgroup 2</u>						
Forward voltage	4011	Pulse width ≤ 8.3 ms and duty cycle ≤ 2 percent.	V_F			
1N6073 thru 1N6075		$I_{FM} = 9.4$ A dc			2.04	V dc
1N6076 thru 1N6078		$I_{FM} = 18.8$ A dc			1.76	V dc
1N6079 thru 1N6081		$I_{FM} = 37.7$ A dc			1.50	V dc
Reverse current leakage	4016	DC method; $V_R = \text{rated } V_R$ (see 1.3)	I_R			
1N6073 thru 1N6075					1.0	$\mu\text{A dc}$
1N6076 thru 1N6078					5.0	$\mu\text{A dc}$
1N6079 thru 1N6081					10.0	$\mu\text{A dc}$
Breakdown voltage	4021	$I_R = 100 \mu\text{A dc}$	$V_{(BR)R}$			
1N6073, 1N6076, 1N6079				60		V dc
1N6074, 1N6077, 1N6080				110		V dc
1N6075, 1N6078, 1N6081				160		V dc
<u>Subgroup 3</u>						
High temperature operation:		$T_A = +100^\circ\text{C}$				
Reverse current leakage	4016	DC method; $V_R = \text{rated } V_R$ (see 1.3)	I_{R2}		25	$\mu\text{A dc}$
1N6073 thru 1N6075					50.0	$\mu\text{A dc}$
1N6076 thru 1N6078					100.0	$\mu\text{A dc}$
1N6079 thru 1N6081					500.0	$\mu\text{A dc}$
<u>Subgroup 4</u>						
Reverse recovery time		See 4.5.4 and figure 3.	t_{rr}		30	ns
Capacitance	4001	$V_R = 12\text{ V}; f \geq 100\text{ KHZ}$ $V_{SIG} \leq 200\text{ mV (pk)}$	C_J			
1N6073 thru 1N6075					24	pF
1N6076 thru 1N6078					58	pF
1N6079 thru 1N6081					230	pF
<u>Subgroups 5, 6, and 7</u>						
Not applicable						

1/ For sampling plan, see MIL-PRF-19500.

TABLE II. Groups A, B and C electrical measurements. 1/ 2/

Step	Inspection	MIL-STD-750		Symbol	Limits		Unit
		Method	Conditions		Min	Max	
1.	Forward voltage	4011	Pulse width \leq 8.3 ms and duty cycle \leq 2 percent.	V_F			
	1N6073 thru 1N6075		$I_{FM} = 9.4$ A dc			2.04	V dc
	1N6076 thru 1N6078		$I_{FM} = 18.8$ A dc			1.76	V dc
	1N6079 thru 1N6081		$I_{FM} = 37.7$ A dc			1.50	V dc
2.	Reverse current	4016	DC method $V_R = \text{rated } V_R$ (see 1.3)	I_R			
	1N6073 thru 1N6075					1.0	$\mu\text{A dc}$
	1N6076 thru 1N6078					5.0	$\mu\text{A dc}$
	1N6079 thru 1N6081					10.0	$\mu\text{A dc}$
3.	Reverse current	4016	DC method; $V_R = \text{rated } V_R$ (see 1.3)	ΔI_R		<u>3/</u>	
	1N6073 thru 1N6075					.250	$\mu\text{A dc}$
	1N6076 thru 1N6078					1.0	$\mu\text{A dc}$
	1N6079 thru 1N6081					5.0	$\mu\text{A dc}$
4.	Breakdown voltage	4021	$I_R = 100$ $\mu\text{A dc}$	$V_{(BR)R}$			
	1N6073, 1N6076, 1N6079				60		V dc
	1N6074, 1N6077, 1N6080				110		V dc
	1N6075, 1N6078, 1N6081				160		V dc
5.	Forward voltage	4011	Pulse width \leq 8.3 ms and duty cycle \leq 2 percent.	ΔV_F			V dc
	1N6073 thru 1N6075		$I_{FM} = 9.4$ A dc				
	1N6076 thru 1N6078		$I_{FM} = 18.8$ A dc				
	1N6079 thru 1N6081		$I_{FM} = 37.7$ A dc				
						± 0.1 V dc maximum change from the previous measured value	

See footnotes at end of table.

TABLE II. Groups A, B and C electrical measurements 1/ 2/ - Continued.

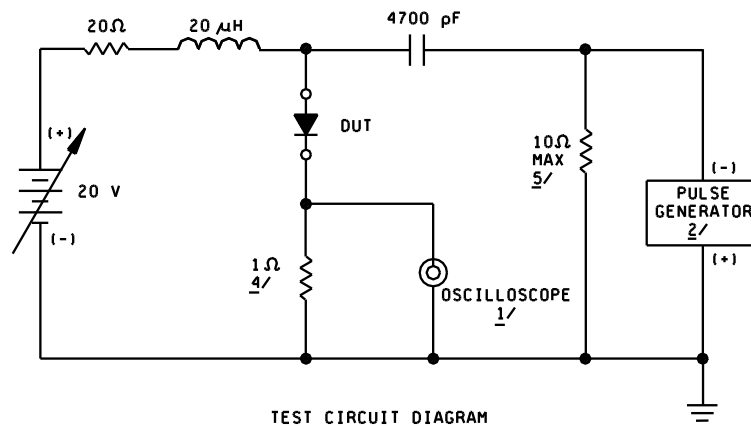
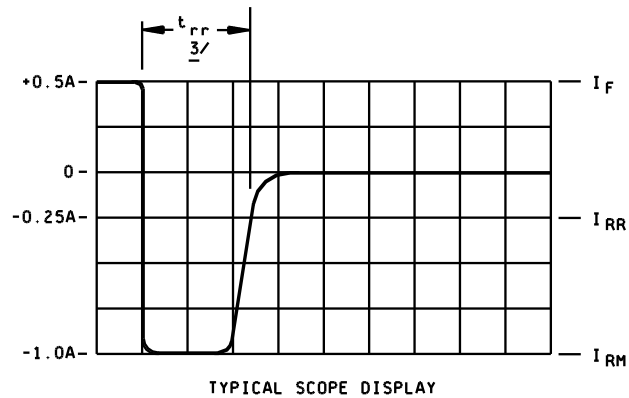
1/ The electrical measurements for table VIb (JAN, JANTX, and JANTXV) of MIL-PRF-19500 are as follows:

- a. Subgroup 2, see table II herein, steps 1 and 2.
- b. Subgroup 3, see table II herein, steps 1, 2, 3, and 5.
- c. Subgroup 6, see table II herein, steps 1, 2, 3, and 5.

2/ The electrical measurements for table VII of MIL-PRF-19500 are as follows:

- a. Subgroup 2, see table II herein, steps 1 and 2.
- b. Subgroup 3, see table II herein, steps 1 and 2.
- c. Subgroup 6, see table II herein, steps 1, 2, 3, and 5.

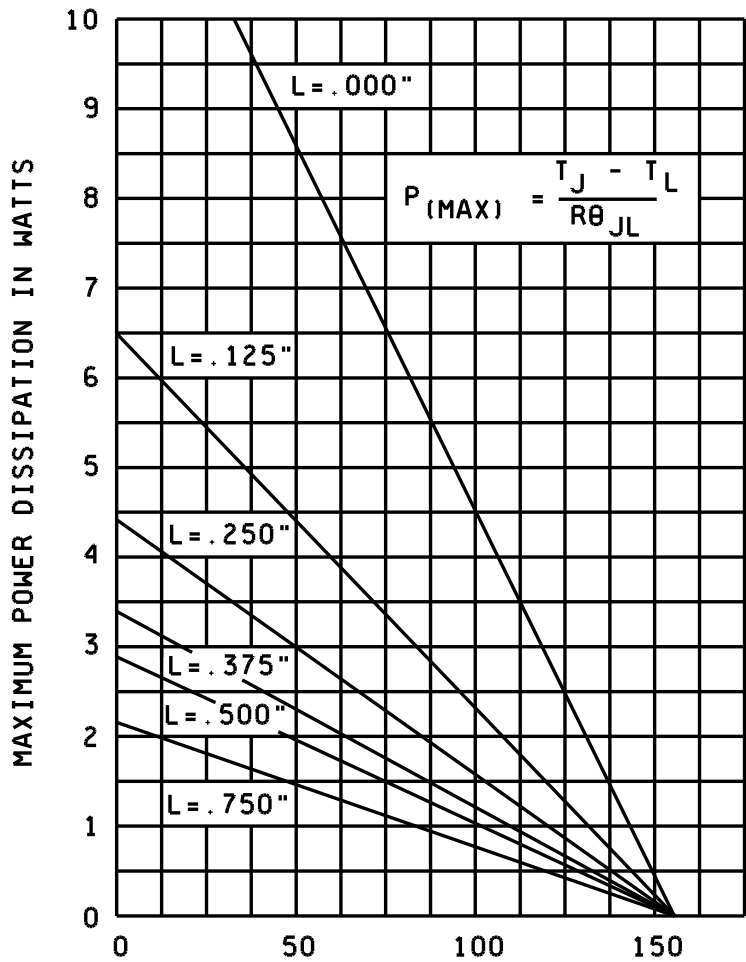
3/ Rated ΔI_R or 100 percent, whichever is greater.



NOTES:

- 1/ Rise time ≤ 350 ps, input impedance 50 ohms, circuit impedance 50 ohms coaxial.
- 2/ Rise time ≤ 250 ps, source impedance = 8 ohms maximum, PRF ≈ 0.5 kHz, $P_W \geq 40$ ns.
- 3/ Recovery conditions: 0.5 A forward current to 1.0 A reverse current. Recovery time measured when rectifier recovers to 0.25 A.
- 4/ Constructed from 10-10 ohm resistors 1/8 watt.
- 5/ Constructed from 10-100 ohm resistors 1/8 watt.

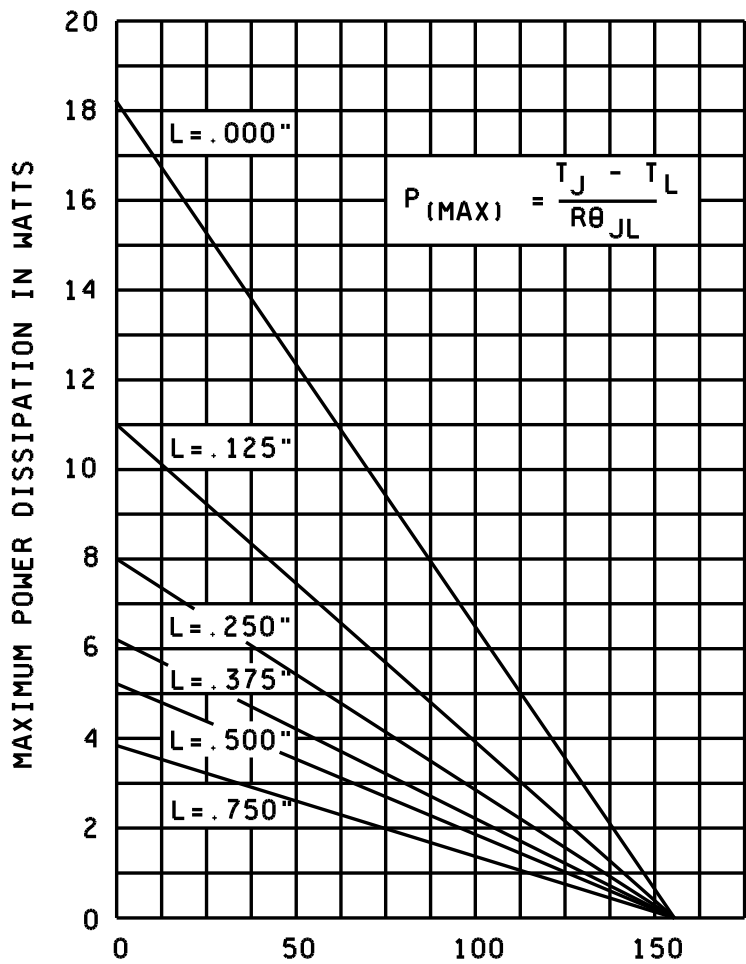
FIGURE 3. Reverse recovery time test circuit and characteristic waveform.



Maximum lead temperature in °C (T_L at point d from body (see table below).
For maximum operating junction temperature with equal two-lead conditions.

L	$R_{\Theta_{J-L}}$
Dimensions	°C/W
0.000 (0.00 mm)	13
0.125 (3.18 mm)	24
0.250 (6.35 mm)	35
0.375 (9.52 mm)	46
0.500 (12.7 mm)	54
0.750 (19.1 mm)	70

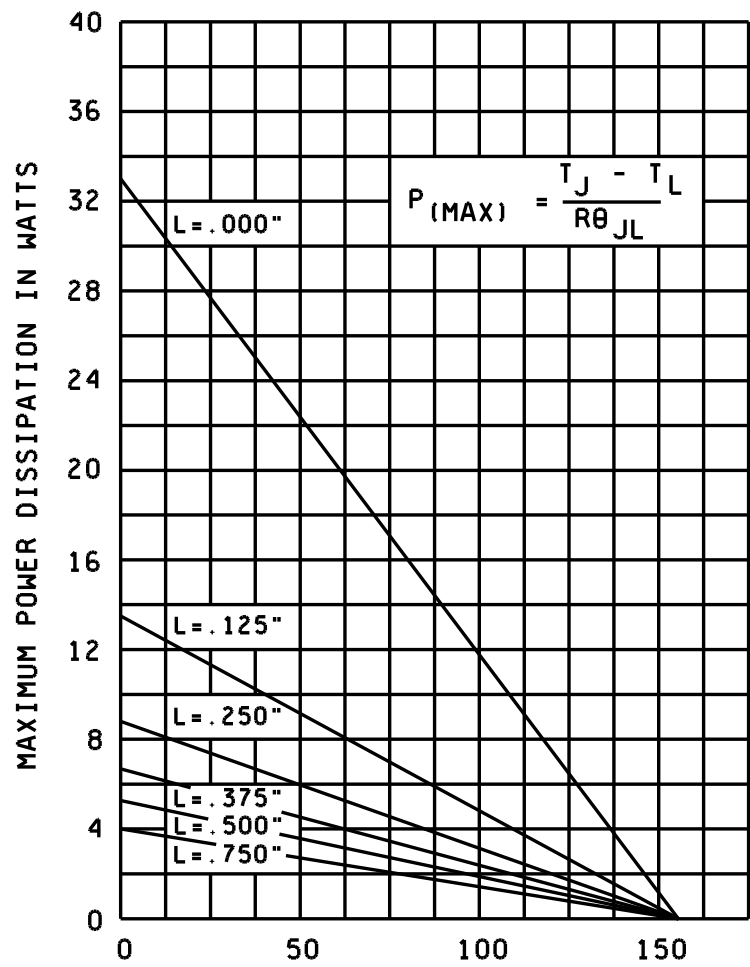
FIGURE 4. Power derating curves maximum power in watts vs lead temperature for 1N6073, 1N6074, and 1N6075.



Maximum lead temperature in °C (T_L at point d from body (see table below).
For maximum operating junction temperature with equal two-lead conditions.

L	$R_{\Theta_{J-L}}$
Dimensions	°C/W
0.000 (0.00 mm)	8.5
0.125 (3.18 mm)	14.0
0.250 (6.35 mm)	19.5
0.375 (9.52 mm)	25.0
0.500 (12.7 mm)	30.0
0.750 (19.1 mm)	40.0

FIGURE 5. Power derating curves maximum power in watts vs lead temperature for 1N6076, 1N6077, and 1N6078.



Maximum lead temperature in °C (T_L at point d from body (see table below).
For maximum operating junction temperature with equal two-lead conditions.

L	$R_{\Theta_{JL}}$
Dimensions	°C/W
0.000 (0.00 mm)	5.0
0.125 (3.18 mm)	11.5
0.250 (6.35 mm)	17.5
0.375 (9.52 mm)	23.5
0.500 (12.7 mm)	29.0
0.750 (19.1 mm)	40.0

FIGURE 6. Power derating curves maximum power in watts vs lead temperature for 1N6079, 1N6080, and 1N6081.

5. PACKAGING

5.1 Packaging. For acquisition purposes, the packaging requirements shall be as specified in the contract or order (see 6.2). When actual packaging of material is to be performed by DoD personnel, these personnel need to contact the responsible packaging activity to ascertain requisite packaging requirements. Packaging requirements are maintained by the Inventory Control Points' packaging activity within the Military Department or Defense Agency, or within the Military Departments' System Command. Packaging data retrieval is available from the managing Military Departments' or Defense Agency's automated packaging files, CD-ROM products, or by contacting the responsible packaging activity.

5.2 Marking. Unless otherwise specified (see 6.2), marking shall be in accordance with MIL-STD-129.

6. NOTES

(This section contains information of a general or explanatory nature that may be helpful, but is not mandatory).

6.1 Notes. The notes specified in MIL-PRF-19500 are applicable to this specification.

6.2 Acquisition requirements. Acquisition documents should specify the following:

- a. Issue of DODISS to be cited in the solicitation.
- b. Lead finish as applicable (see 3.3.2).
- c. Type designation and quality product assurance level.
- d. For die acquisition, the JANHC letter version should be specified (see figure 2) and 6.5.

6.3 Thermal impedance. Device power capability with lead dissipators or body forced air cooling, may be determined from figures 3, 4, and 5, which shows maximum power dissipation in watts versus lead temperature in °C as a function of the distance "L" from the diode body at which lead temperature is measured.

6.4 Changes from previous issue. Marginal notations are not used in this revision to identify changes with respect to the previous issue, due to the extensiveness of the changes.

6.5 Suppliers of JANHC die. The qualified JANHC suppliers with the applicable letter version (example, JANHCA1N6073) will be identified on the QPL.

JANHC ordering information		
PIN	Manufacturer	
	33178	--
1N6073 through 1N6081	JANHCA1N6073 through JANHCA1N6081	-- --

6.6 Qualification. With respect to products requiring qualification, awards will be made only for products which are, at the time of award of contract, qualified for inclusion in Qualified Products List QPL-19500 whether or not such products have actually been so listed by that date. The attention of the contractors is called to these requirements, and manufacturers are urged to arrange to have the products that they propose to offer to the Federal Government tested for qualification in order that they may be eligible to be awarded contracts or purchase orders for the products covered by this specification. Information pertaining to qualification of products may be obtained from Defense Supply Center Columbus, DSCC-VAT, Columbus, OH 43216.

MIL-PRF-19500/503B

CONCLUDING MATERIAL

Custodians:
Army - CR
Air Force - 17

Review activity:
Air Force - 10, 80, 85, 99

Preparing activity:
DLA - CC
(Project 5961-1734)

STANDARDIZATION DOCUMENT IMPROVEMENT PROPOSAL

INSTRUCTIONS

1. The preparing activity must complete blocks 1, 2, 3, and 8. In block 1, both the document number and revision letter should be given.
2. The submitter of this form must complete blocks 4, 5, 6, and 7.
3. The preparing activity must provide a reply within 30 days from receipt of the form.

NOTE: This form may not be used to request copies of documents, nor to request waivers, or clarification of requirements on current contracts. Comments submitted on this form do not constitute or imply authorization to waive any portion of the referenced document(s) or to amend contractual requirements.

I RECOMMEND A CHANGE:

1. DOCUMENT NUMBER
MIL-PRF-19500/503B

2. DOCUMENT DATE
(YYMMDD) 97/09/12

3. DOCUMENT TITLE SEMICONDUCTOR DEVICE, DIODE, SILICON, POWER RECTIFIER, ULTRA FAST RECOVERY, TYPES 1N6073 THROUGH 1N6081, JAN, JANTX, JANTXV, AND JANHC

4. NATURE OF CHANGE (Identify paragraph number and include proposed rewrite, if possible. Attach extra sheets as needed.)

5. REASON FOR RECOMMENDATION

6. SUBMITTER

a. NAME (Last, First, Middle initial)

b. ORGANIZATION

c. ADDRESS (Include Zip Code)

d. TELEPHONE (Include Area Code)
(1) Commercial
(2) AUTOVON
(If applicable)

7. DATE SUBMITTED
(YYMMDD)

8. PREPARING ACTIVITY

a. NAME
Alan Barone

b. TELEPHONE (Include Area Code)
(1) Commercial (2) AUTOVON
614-692-0510 850-0510

c. ADDRESS (Include Zip Code)
Defense Supply Center Columbus
ATTN: DSCC-VAT
Columbus, OH 43216-5000

IF YOU DO NOT RECEIVE A REPLY WITHIN 45 DAYS, CONTACT:
Defense Quality and Standardization Office
5203 Leesburg Pike, Suite 1403,
Falls Church, VA 22041-3466
Telephone (703) 756-2340 AUTOVON 289-2340